**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Logic-level compatible
- Extended temperature range T<sub>i</sub> = 175 °C
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)

## 3. Applications

- Relay driver
- · High-speed line driver
- Low-side load switch
- · Switching circuits

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	3.5	Α
Static chara	acteristics				'	'	
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 3.5 \text{ A}; T_j = 25 \text{ °C}$		-	37	49	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



**60 V, N-channel Trench MOSFET** 

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D -
2	S	source	3	
3	D	drain	1 2 SOT23	G S 017aaa255

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PMV37ENE		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PMV37ENE	%3M

[1] % = placeholder for manufacturing site code

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## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	3.5	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	2.5	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	14	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	710	mW
			[1]	-	1.3	W
		T <sub>sp</sub> = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	diode		'	'		
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	1.3	А

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

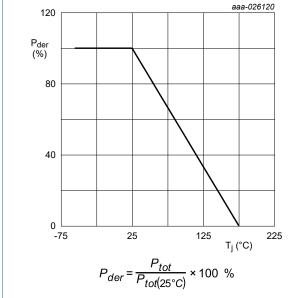


Fig. 1. Normalized total power dissipation as a function of junction temperature

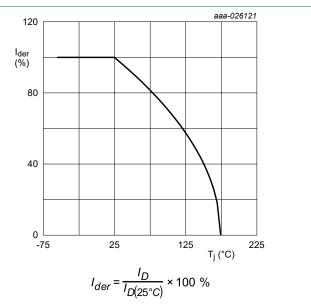


Fig. 2. Normalized continuous drain current as a function of junction temperature

## **60 V, N-channel Trench MOSFET**

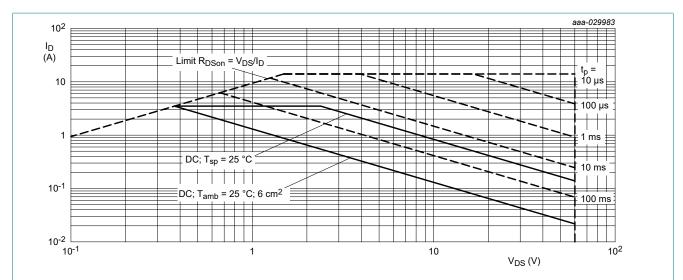


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

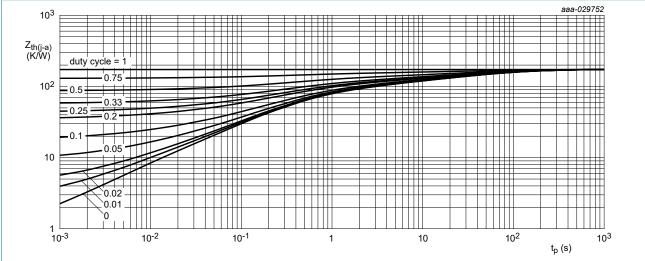
60 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

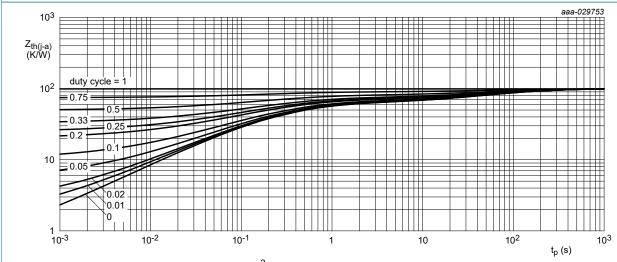
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	175	210	K/W
junction to ambient		[2]	-	95	115	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

**60 V, N-channel Trench MOSFET** 

## 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 3.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	37	49	mΩ
resistance	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3.5 A; T <sub>j</sub> = 175 °C	-	80	106	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.1 A; T <sub>j</sub> = 25 °C	-	45	64	mΩ
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 3.5 \text{ A}; T_j = 25 \text{ °C}$	-	18.2	-	S
$R_G$	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 3.5 \text{ A}; V_{GS} = 10 \text{ V};$	-	8.8	13	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.1	-	nC
Q <sub>GD</sub>	gate-drain charge	1	-	1.8	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 30 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	450	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	49	-	pF
C <sub>rss</sub>	reverse transfer capacitance	_	-	30	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; I_D = 3.5 \text{ A}; V_{GS} = 10 \text{ V};$	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	7	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	13	-	ns
t <sub>f</sub>	fall time	1	-	4	-	ns
Source-dra	in diode	•			-	
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 1.3 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C		0.8	1.2	V

#### 60 V, N-channel Trench MOSFET

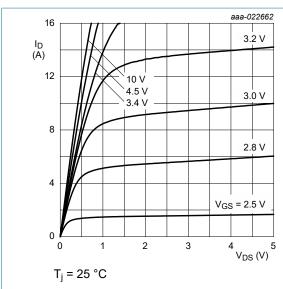


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

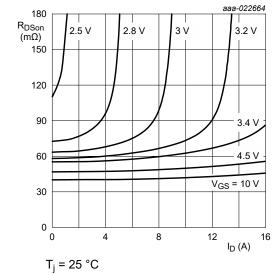


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

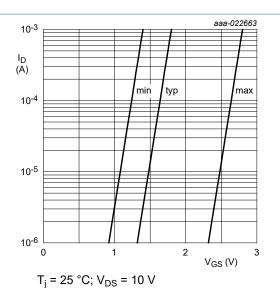


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

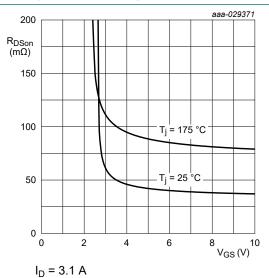


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### **60 V, N-channel Trench MOSFET**

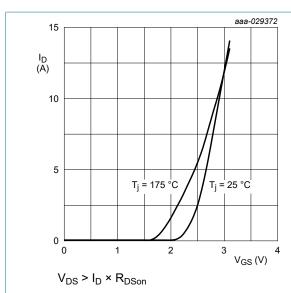


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

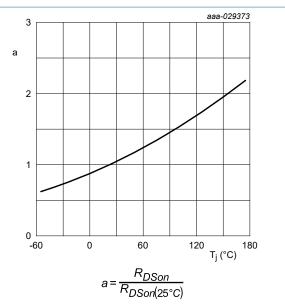


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

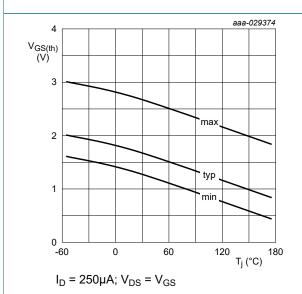
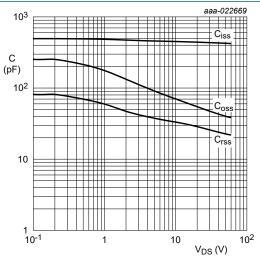


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 60 V, N-channel Trench MOSFET

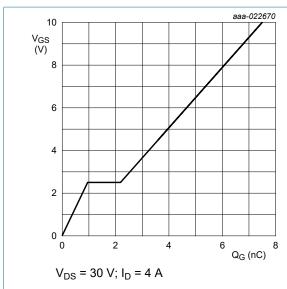


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$ 

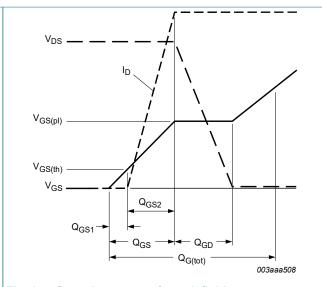


Fig. 15. Gate charge waveform definitions

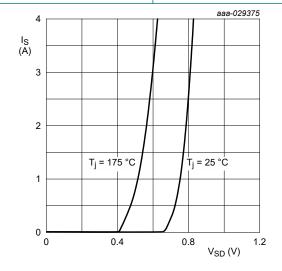
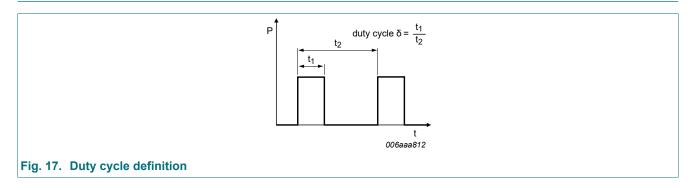


Fig. 16. Source current as a function of source-drain voltage; typical values

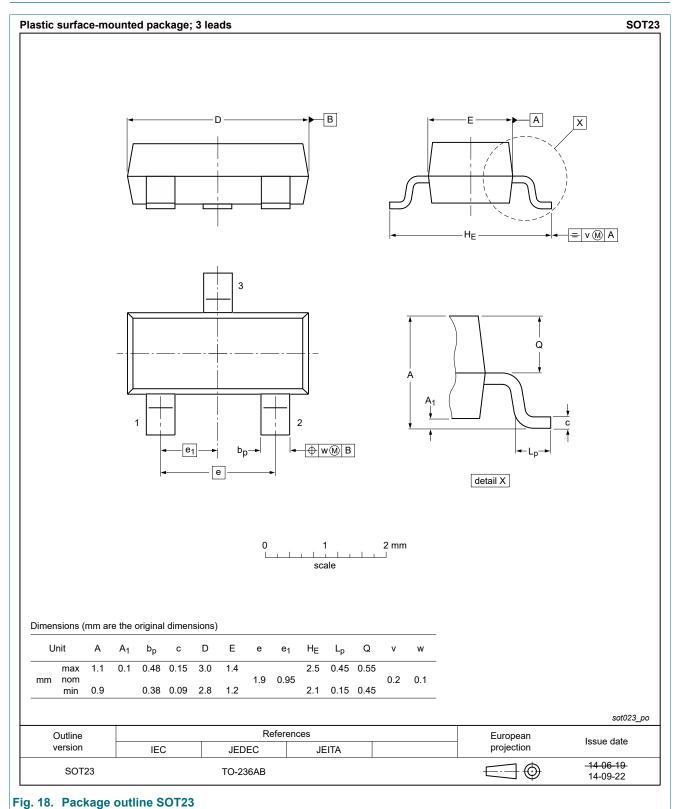
**60 V, N-channel Trench MOSFET** 

## 11. Test information



#### 60 V, N-channel Trench MOSFET

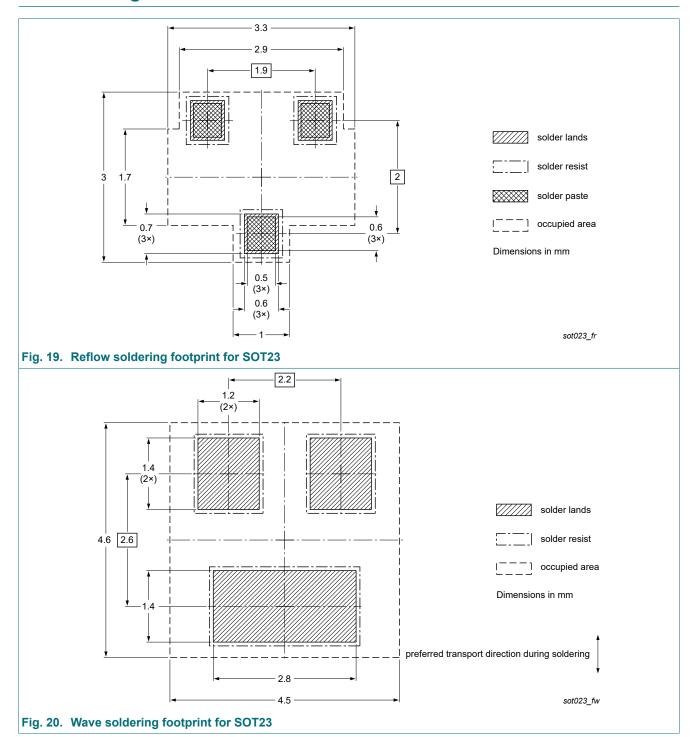
## 12. Package outline



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60 V, N-channel Trench MOSFET

## 13. Soldering



**60 V, N-channel Trench MOSFET** 

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV37ENE v.1	20211129	Product data sheet	-	-

#### 60 V, N-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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WMJ80N60C4 BXP2N20L BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR DMNH15H110SK3-13
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